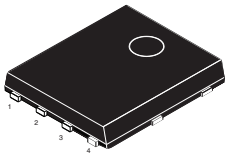
STL40N10F7

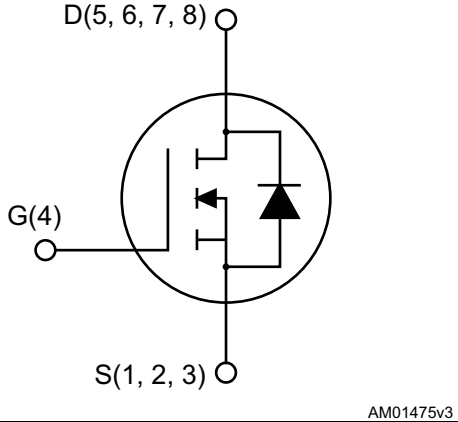
N-channel 100 V, 0.020 Ω typ., 10 A, STripFET™ VII DeepGATE™ Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet – preliminary data



PowerFLAT™ 5x6

Figure 1. Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max	I_D	P_{TOT}
STL40N10F7	100 V	0.024 Ω	20 A	5 W(1)

1. The value is rated according $R_{thj\text{-}pcb}$

- Ultra low on-resistance
- 100% avalanche tested

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the 7th generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest $R_{DS(on)}$ in all packages.

Table 1. Device summary

Order code	Marking	Package	Packaging
STL40N10F7	40N10F7	PowerFLAT™ 5x6	Tape and reel

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	± 20	V
I_D (1)	Drain current (continuous) at T_C = 25 °C	40	A
I_D (1)	Drain current (continuous) at T_C = 100 °C	28	A
I_D (2)	Drain current (continuous) at T_{pcb} = 25 °C	10	A
I_D (2)	Drain current (continuous) at T_{pcb}=100 °C	7	A
I_{DM} (2)(3)	Drain current (pulsed)	40	A
P_{TOT} (1)	Total dissipation at T_C = 25 °C	70	W
P_{TOT} (2)	Total dissipation at T_{pcb} = 25 °C	5	W
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 175	°C

1. This value is rated according to $R_{thj\text{-}c}$.
2. This value is rated according to $R_{thj\text{-}pcb}$.
3. Pulse width limited by safe operating area.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	2.08	°C/W
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb	31	°C/W

1. When mounted on FR-4 board of 1 inch², 2oz Cu, t < 10 sec

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0, I_D = 250 µA	100			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0, V_{DS} = 100 V			10	µA
		V_{GS} = 0, V_{DS} = 100 V, T_C=125 °C			100	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0, V_{GS} = +20 V			100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 10 A		0.02	0.024	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 50 V, f = 1 MHz, V_{GS} = 0	-	1320	-	pF
C_{oss}	Output capacitance		-	230	-	pF
C_{rss}	Reverse transfer capacitance		-	8	-	pF
Q_g	Total gate charge	V_{DD} = 50 V, I_D = 20 A, V_{GS} = 10 V (see *Figure 3*)	-	14	-	nC
Q_{gs}	Gate-source charge		-	TBD	-	nC
Q_{gd}	Gate-drain charge		-	TBD	-	nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 50 V, I_D = 10 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 2*)	-	TBD	-	ns
t_r	Rise time		-	TBD	-	ns
$t_{d(off)}$	Turn-off delay time		-	TBD	-	ns
t_f	Fall time		-	TBD	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-	-	20	A
I_{SDM} (1)	Source-drain current (pulsed)		-	-	80	A
V_{SD} (2)	Forward on voltage	I_{SD} = 20 A, V_{GS} = 0	-	-		V
t_{rr}	Reverse recovery time	I_{SD} = 20 A, di/dt = 100 A/µs V_{DD} = 80 V, T_J=150 °C	-	-		ns
Q_{rr}	Reverse recovery charge		-	-		nC
I_{RRM}	Reverse recovery current		-	-		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 µs, duty cycle 1.5%.

3 Test circuits

Figure 2. Switching times test circuit for resistive load

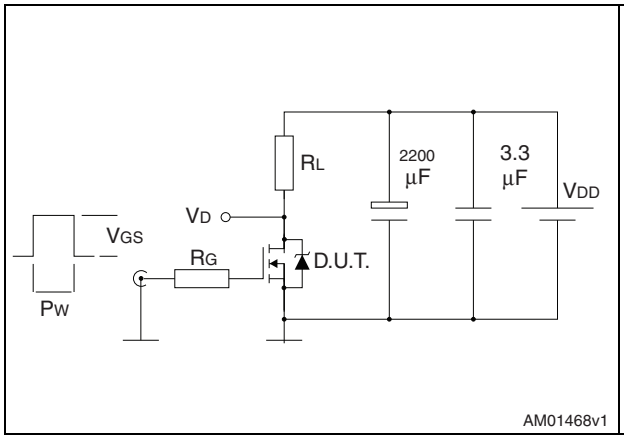


Figure 3. Gate charge test circuit

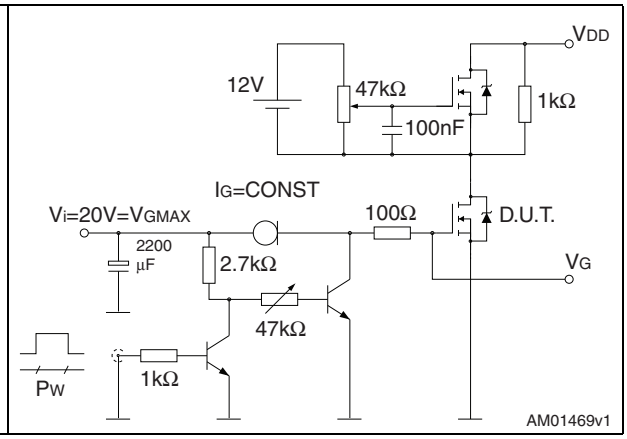


Figure 4. Test circuit for inductive load switching and diode recovery times

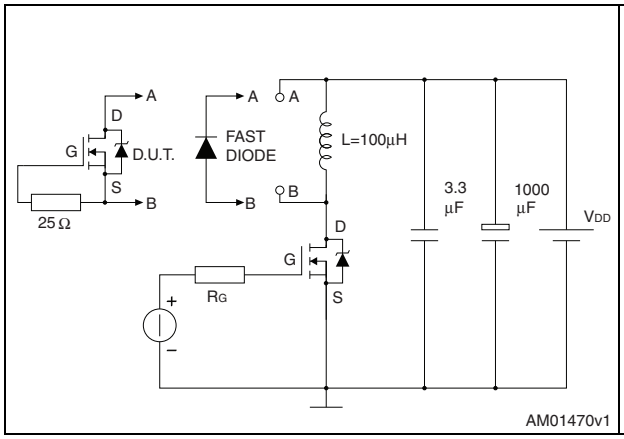


Figure 5. Unclamped inductive load test circuit

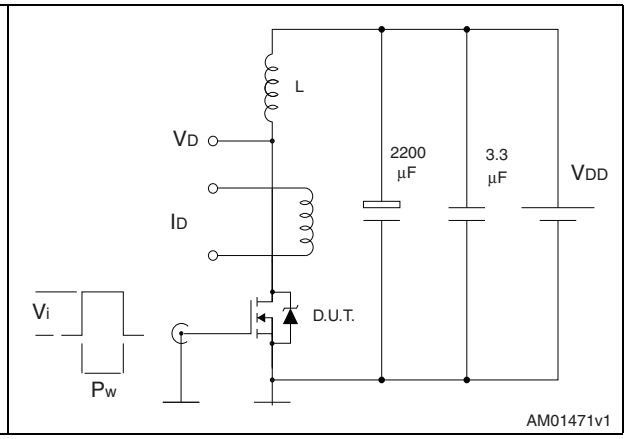


Figure 6. Unclamped inductive waveform

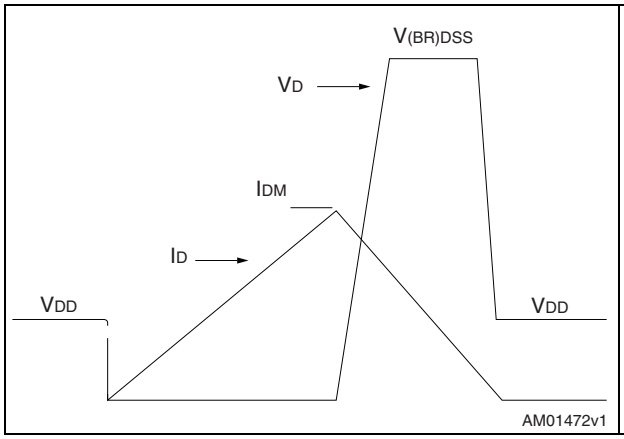
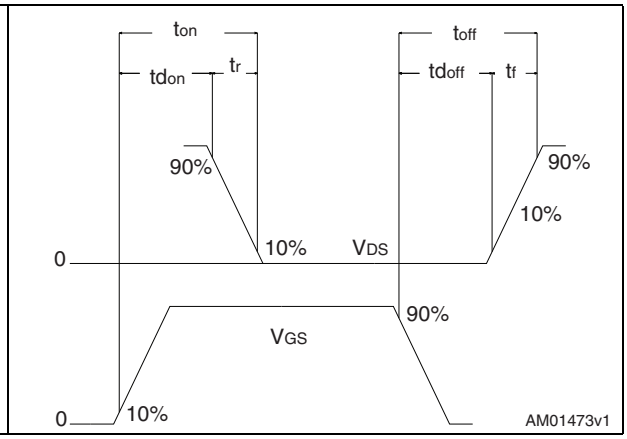


Figure 7. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*.
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Table 8. PowerFLAT 5x6 type S-R mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D	5.00	5.20	5.40
E	5.95	6.15	6.35
D2	4.11		4.31
E2	3.50		3.70
e		1.27	
L	0.60		0.80
K	1.275		1.575

Figure 8. PowerFLAT 5x6 type S-R drawing

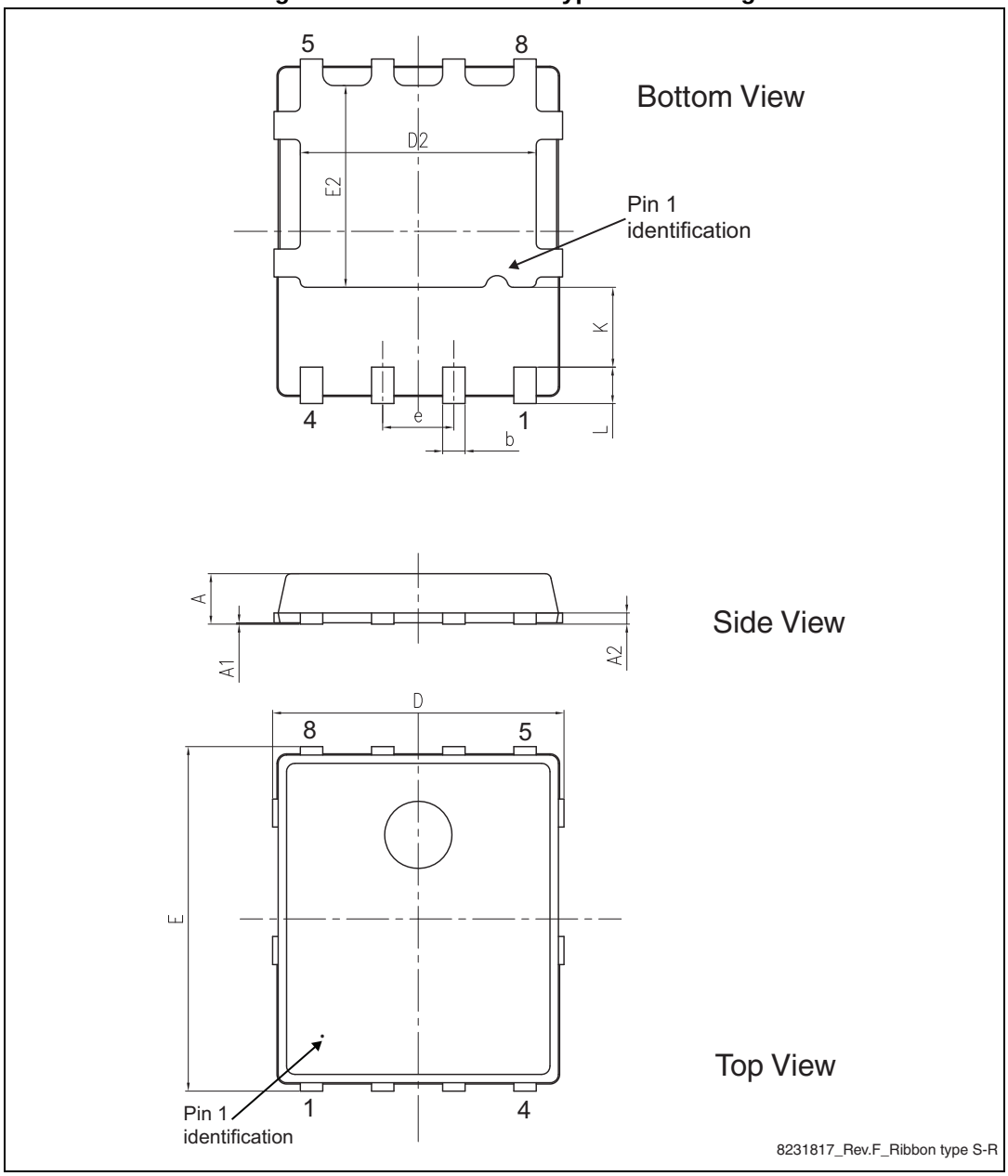
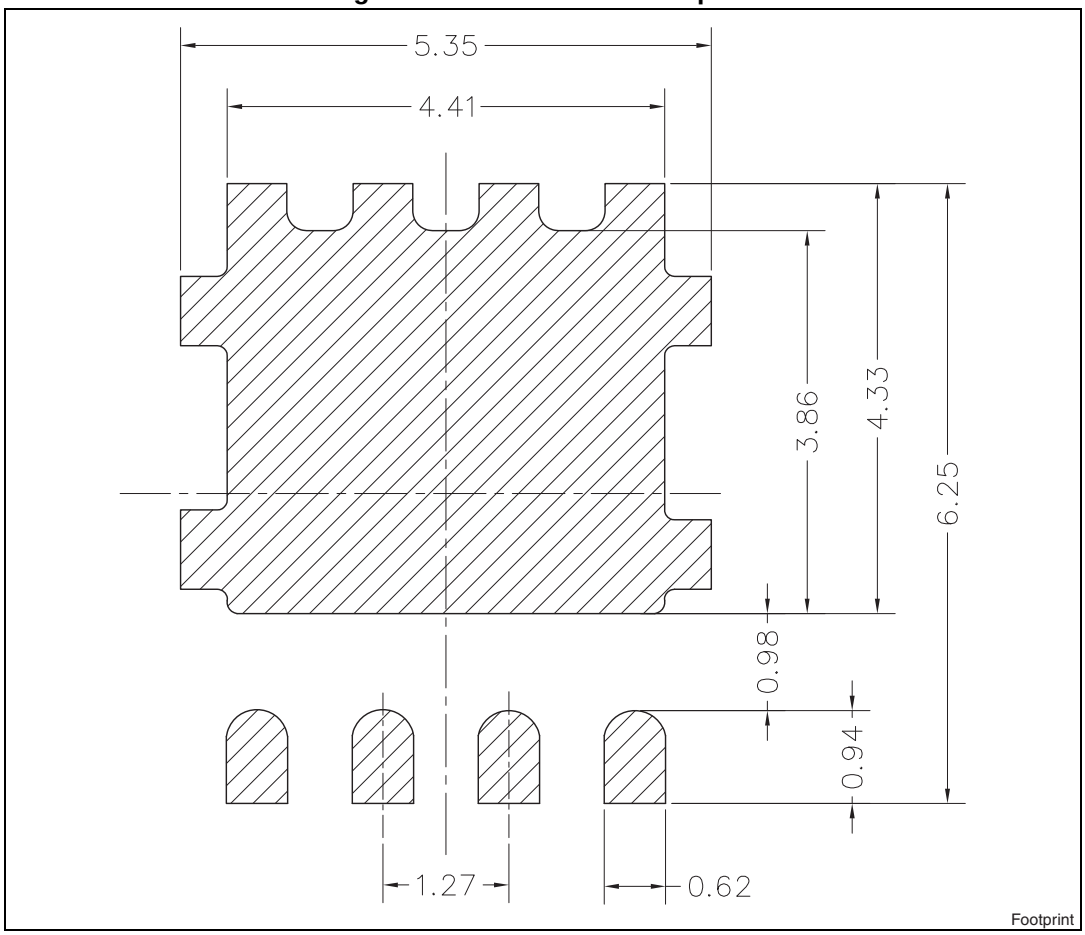


Figure 9. Recommended footprint



5 Packaging mechanical data

Figure 10. PowerFLAT™ 5x6 tape[(a)]

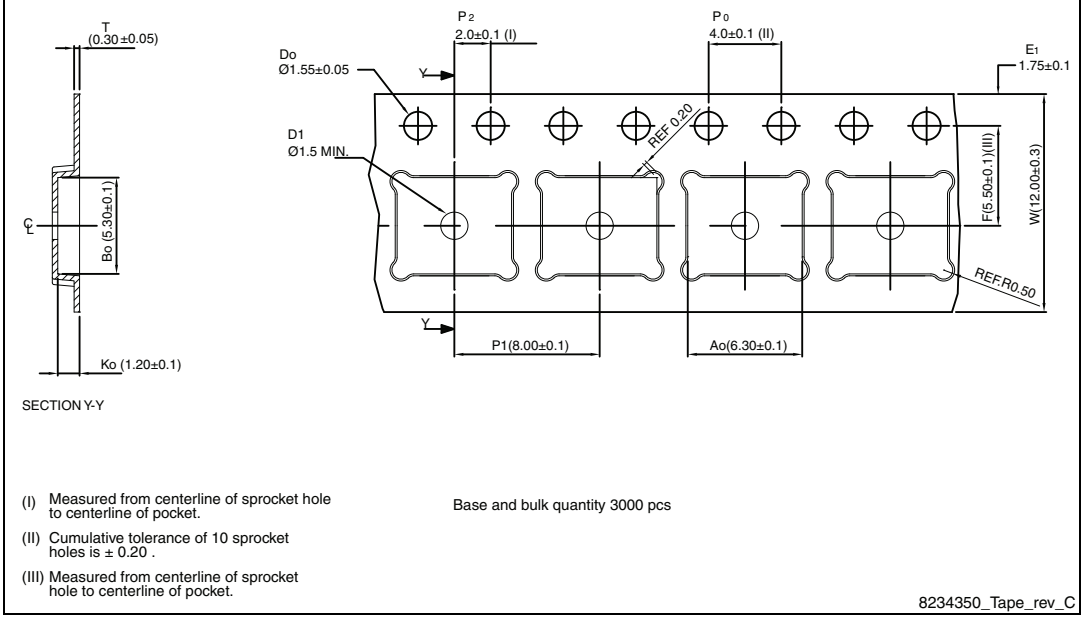
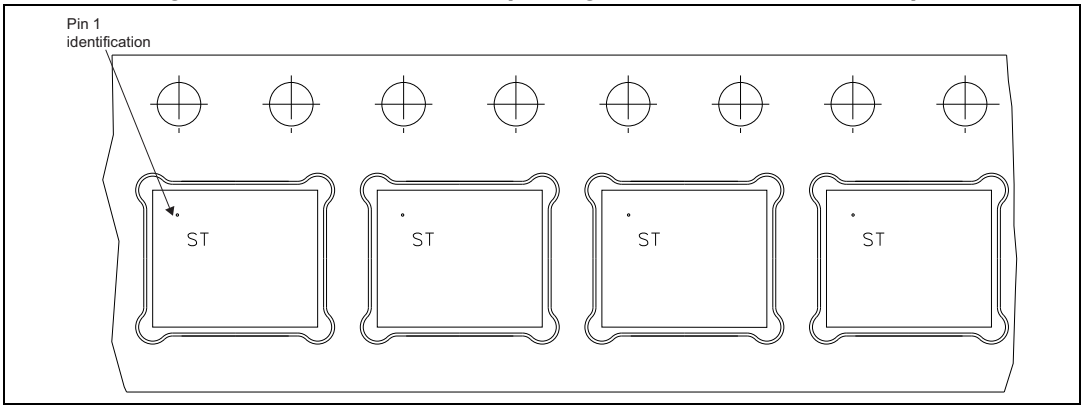
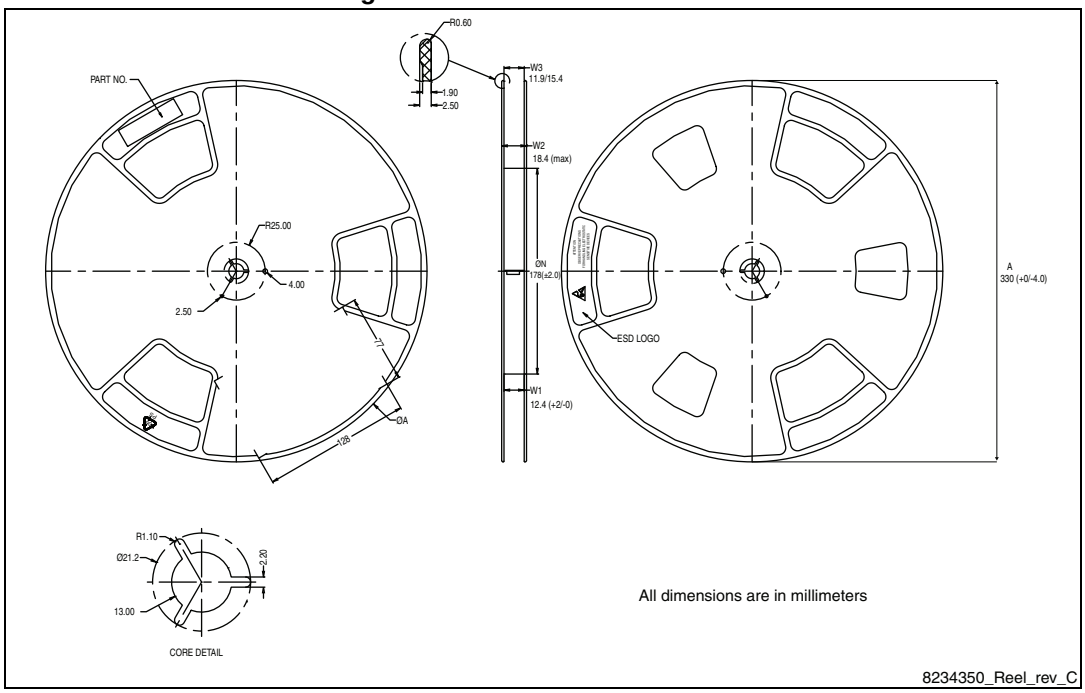


Figure 11. PowerFLAT™ 5x6 package orientation in carrier tape



a. All dimensions are in millimeters.

Figure 12. PowerFLAT™ 5x6 reel



6 Revision history

Table 9. Document revision history

Date	Revision	Changes
20-May-2013	1	First release.

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